



ON Semiconductor®

3LN01M

## SPICE PARAMETER

### Nch MOS FET

model : BSIM3V3.2

Parameter	Value	Parameter	Value	Parameter	Value
LEVEL	8				
VERSION	3.2	TNOM	27	TOX	3.0E-08
VTH0	0.82	K1	1.96	K2	-0.04
NLX	1.70E-07	DVT0	3.12	DVT1	0.58
DVT2	-0.01	U0	680	UA	1.24E-09
UB	1.00E-21	VSAT	1.75E+05	A0	0.04
AGS	0.2	A1	0	A2	1
RDSW	2.72E+03	PRWG	-1.60E-02	WR	0.82
WINT	-0.00086	LINT	1.86E-07	VOFF	-0.133
NFACTOR	0.52	CIT	0	CDSC	2.40E-07
CDSCD	0	ETA0	0.02	DSUB	0.96
PCLM	1.35	PDIBLC1	0.06	PDIBLC2	4.00E-04
DROUT	0.96	PSCBE1	2.40E+09	PSCBE2	1.00E-05
PVAG	0.01	DELTA	0.03	NGATE	1.00E+22
MOBMOD	1	NQSMOD	0	NOIMOD	1
CAPMOD	3	XPART	0.5	CGSO	1.40E-10
CGDO	1.50E-10	CGBO	0	CGSL	0
CGDL	4.00E-09	CKAPPA	0.8	CF	0
CLC	1.00E-07	CLE	0.8	DWC	0
DLC	-2.00E-07	NOFF	3.6	VOFFCV	-0.4
ACDE	1	MOIN	15	CJ	2.84E-03
MJ	0.36	PB	0.68	JS	3.00E-05
NJ	1	XTI	3	IJTH	0
KT1	-0.4	UTE	-1.1	PRT	3.94E+03
AT	3.30E+04				

Temp = 27 deg  
 L = 1.0E-6 m  
 W = 3564E-6 m  
 AD = 3564E-12 m2  
 RG = 4093 ohm  
 RB = 0.8 ohm

Date : 2012/08/30

\*Information herein is for example only ;  
 It is not guaranteed for volume production.

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